Analog Power AM7336N

N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

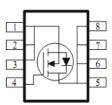
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
30	9 @ V _{GS} = 4.5V	16.2		
30	11 @ V _{GS} = 2.5V	14.6		







DFN3x3-8L



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			30	V			
Gate-Source Voltage	V_{GS}	±8	V				
Continuous Drain Current a	T _A =25°C	1	16.2	А			
Continuous Drain Current	T _A =70°C	I _D	12.2				
Pulsed Drain Current ^b		I_{DM}	50				
Continuous Source Current (Diode Conduction) ^a		I _S	2.1	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	3.5	W			
Power Dissipation	T _A =70°C	' D	2	V V			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
Maximum Junction-to-Ambient	Steady State	IXOJA	81	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	8.1			Α	
Drain-Source On-Resistance	r	$V_{GS} = 4.5 \text{ V}, I_D = 13.6 \text{ A}$	(9	mΩ	
Dialii-30dice Oil-Resistance	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 11.7 \text{ A}$			11	11177	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 13.6 \text{ A}$		20		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 1.1 \text{ A}, V_{GS} = 0 \text{ V}$		0.64		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		21			
Gate-Source Charge	Q_{gs}	$I_{DS} = 13 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 13.6 \text{ A}$		4.4		nC	
Gate-Drain Charge	Q_gd	ID = 13.0 A		7.0			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_1 = 1.2 \Omega,$		17			
Rise Time	t _r	$I_{DS} = 13.0, K_L - 1.2.02,$ $I_D = 13.6 A,$		27		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		90		ns	
Fall Time	t _f	V GEN - 4.5 V, T GEN - 0 12		33			
Input Capacitance	C _{iss}			2238			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		226		pF	
Reverse Transfer Capacitance	C_{rss}			215			

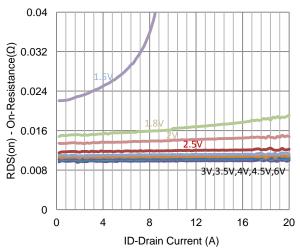
Notes

- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

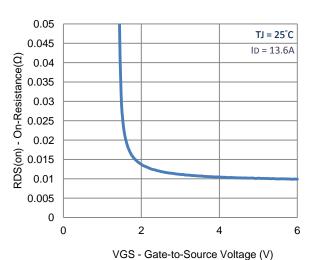
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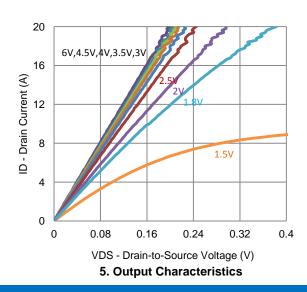
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



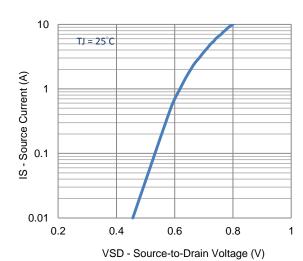
3. On-Resistance vs. Gate-to-Source Voltage



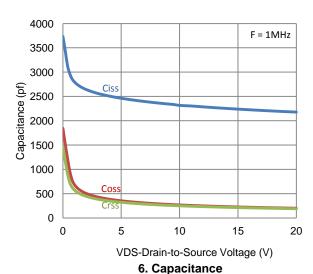
20
TJ = 25°C

16
(V) tue 12
0
0
1 2
3
VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics

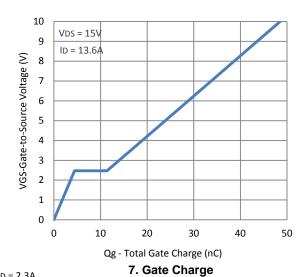


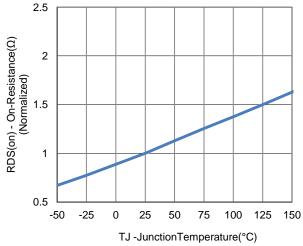
4. Drain-to-Source Forward Voltage

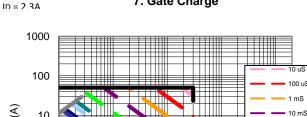


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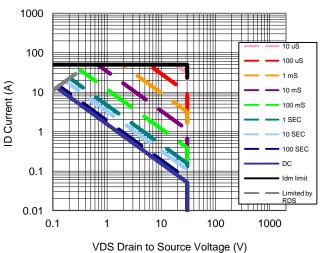
Typical Electrical Characteristics

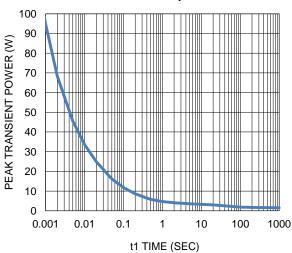






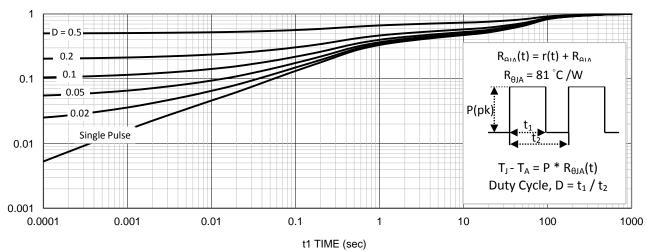






9. Safe Operating Area

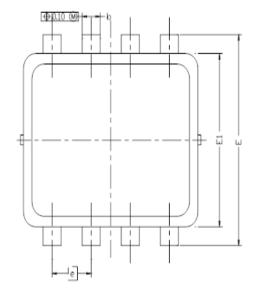
10. Single Pulse Maximum Power Dissipation

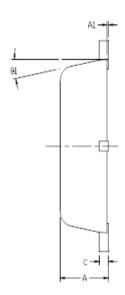


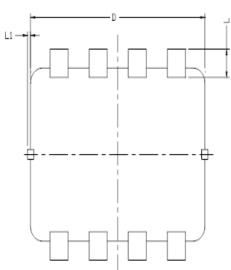
11. Normalized Thermal Transient Junction to Ambient

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Package Information







DIM	MILLIMETERS			INCHES			
DIM.	MIN	NDM	MAX	MIN	NDM	MAX	
А	0.700	0.80	0.900	0.0276	0.0315	0.0354	
A1	0.00		0,05	0,000		0,002	
b	0,24	0.30	0,35	0.009	0.012	0.014	
_	0.08	0.152	0.25	0.003	0,006	0.010	
D	2.90 BSC			0.114 BSC			
E	2.80 BSC			0.110 BSC			
E1	2.30 BSC			0.091 BSC			
9	0	0.65 BSC			0.026 BSC		
L	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0		0.004	
91	0	10	12	0	10	12	